

2N5344 2N5345

HIGH VOLTAGE POWER PNP SILICON TRANSISTORS

... designed for high-voltage switching and amplifier applications.

- High Voltage Ratings — $V_{CEO} = 250$ and 300 Vdc
- Fast Switching Times — Typically Less Than 550 ns
Total @ $V_{CC} = 100$ Vdc
- High Current-Gain-Bandwidth Product —
 $f_T = 60$ MHz (Min) @ $I_C = 100$ mAdc
- Packaged in the Compact, High-Efficiency TO-66 Case

1 AMPERE POWER TRANSISTORS PNP SILICON

250-300 VOLTS
40 WATTS

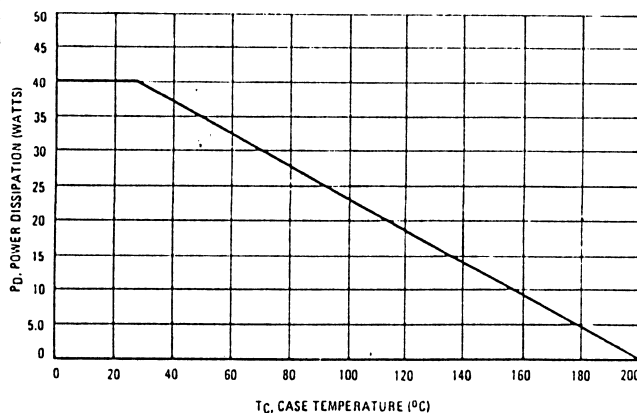
MAXIMUM RATINGS

Rating	Symbol	2N5344	2N5345	Unit
Collector-Emitter Voltage	V_{CEO}	250	300	Vdc
Collector-Base Voltage	V_{CB}	250	300	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Base Current — Continuous	I_B	0.5		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$	P_D	40		Watts
Derate above 25°C		228		mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

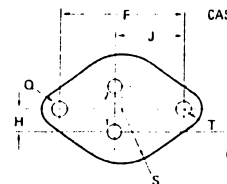
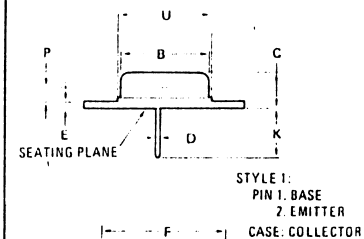
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	4.38	$^\circ\text{C/W}$

FIGURE 1 — POWER-TEMPERATURE DERATING CURVE



Safe Area Curves Are Indicated By Figure 5.
All Limits Are Applicable And Must Be Observed



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
B	11.94	12.70	0.470	0.500
C	6.35	8.64	0.250	0.340
D	0.71	0.86	0.028	0.034
E	1.27	1.91	0.050	0.075
F	24.33	24.43	0.958	0.962
G	4.83	5.33	0.190	0.210
H	2.41	2.67	0.095	0.105
J	14.48	14.99	0.570	0.590
K	9.14	-	0.360	-
P	-	1.27	-	0.050
Q	3.61	3.86	0.142	0.152
S	-	8.89	-	0.350
T	-	3.68	-	0.145
U	-	15.75	-	0.620

All JEDEC Dimensions and Notes Apply.

CASE 80-02
TO-66

